

KA5x0365RN-SERIES

KA5M0365RN, KA5L0365RN Fairchild Power Switch(FPS)

Features

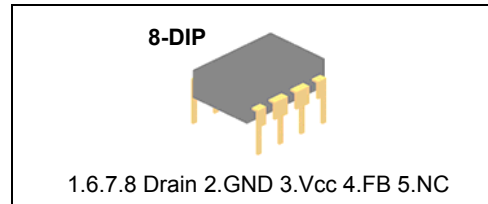
- Precision Fixed Operating Frequency (67/50kHz)
- Low Start-up Current(Typ. 100uA)
- Pulse by Pulse Current Limiting
- Over Current Protection
- Over Voltage Protection (Min. 25V)
- Internal Thermal Shutdown Function
- Under Voltage Lockout
- Internal High Voltage Sense FET
- Auto-Restart Mode

Applications

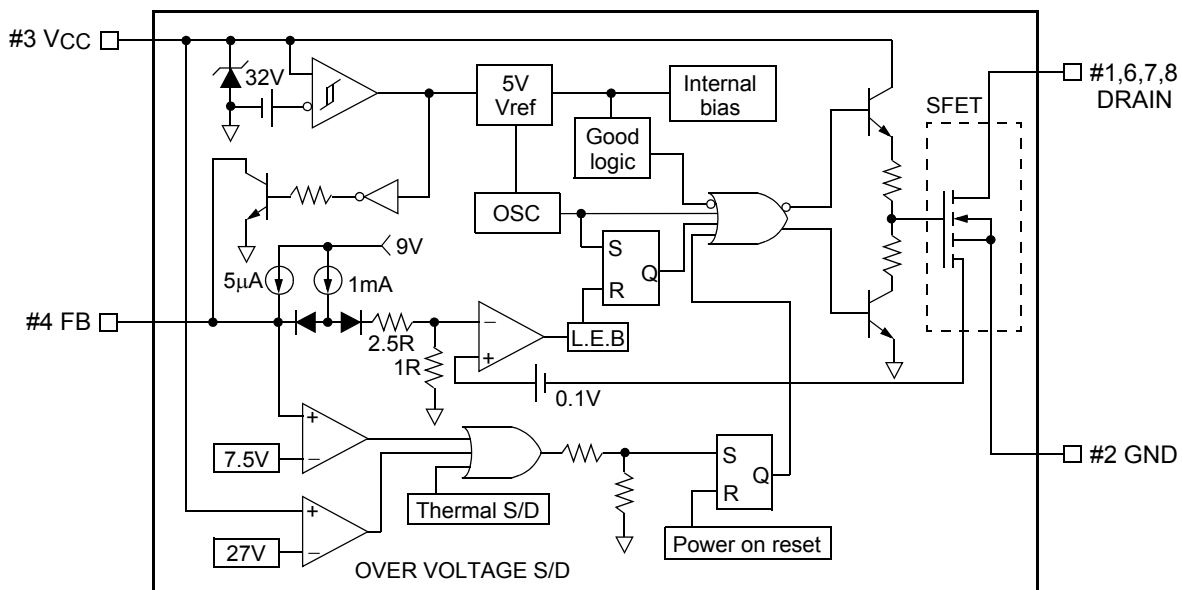
- SMPS for VCR, SVR, STB, DVD & DVCD
- SMPS for Printer, Facsimile & Scanner
- Adaptor for Camcorder

Description

The Fairchild Power Switch(FPS) product family is specially designed for an off-line SMPS with minimal external components. The Fairchild Power Switch(FPS) consists of a high voltage power SenseFET and a current mode PWM IC. Included PWM controller integrates the fixed frequency oscillator, the under voltage lock-out, the leading edge blanking, the optimized gate turn-on/turn-off driver, the thermal shutdown protection, the over voltage protection, and the temperature compensated precision current sources for the loop compensation and the fault protection circuitry. Compared to a discrete MOSFET and a PWM controller or an RCCsolution, a Fairchild Power Switch(FPS) can reduce the total component count, design size and weight and at the same time increase efficiency, productivity, and system reliability. It has a basic platform well suited for the cost effective design in either a flyback converter or a forward converter



Internal Block Diagram



Rev.1.0.6

Absolute Maximum Ratings

(Ta=25°C, unless otherwise specified)

Characteristic	Symbol	Value	Unit
KA5M0365RN, KA5L0365RN			
Drain-Gate Voltage (R _{GS} =1MΩ)	V _{DGR}	650	V
Gate-Source (GND) Voltage	V _{GS}	±30	V
Drain Current Pulsed ⁽¹⁾	I _{DM}	3	ADC
Continuous Drain Current (Ta=25°C)	I _D	0.42	ADC
Continuous Drain Current (Ta=100°C)	I _D	0.28	ADC
Single Pulsed Avalanche Energy ⁽²⁾	E _{AS}	127	mJ
Maximum Supply Voltage	V _{CC,MAX}	30	V
Analog Input Voltage Range	V _{FB}	-0.3 to V _{SD}	V
Total Power Dissipation	P _D	1.56	W
	Derating	0.0125	W/°C
Operating Junction Temperature.	T _J	+160	°C
Operating Ambient Temperature.	T _A	-25 to +85	°C
Storage Temperature Range.	T _{STG}	-55 to +150	°C

Note:

1. Repetitive rating: Pulse width limited by maximum junction temperature
2. L = 51mH, starting T_J = 25°C
3. L = 13μH, starting T_J = 25°C

Electrical Characteristics (SenseFET Part)

(Ta = 25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
KA5M0365RN, KA5L0365RN						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =50μA	650	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =Max. Rating, V _{GS} =0V	-	-	50	μA
		V _{DS} =0.8Max. Rating, V _{GS} =0V, T _C =125°C	-	-	200	μA
Static Drain-Source on Resistance ^(Note)	R _{DS(ON)}	V _{GS} =10V, I _D =0.5A	-	3.6	4.5	Ω
Forward Transconductance ^(Note)	g _{fs}	V _{DS} =50V, I _D =0.5A	2.0	-	-	S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =25V, f=1MHz	-	314.9	-	pF
Output Capacitance	C _{oss}		-	47	-	
Reverse Transfer Capacitance	C _{rss}		-	9	-	
Turn On Delay Time	t _{d(on)}	V _{DD} =0.5BV _{DSS} , I _D =1.0A (MOSFET switching time is essentially independent of operating temperature)	-	11.2	-	nS
Rise Time	t _r		-	34	-	
Turn Off Delay Time	t _{d(off)}		-	28.2	-	
Fall Time	t _f		-	32	-	
Total Gate Charge (Gate-Source+Gate-Drain)	Q _g	V _{GS} =10V, I _D =1.0A, V _{DS} =0.5BV _{DSS} (MOSFET switching time is essentially independent of operating temperature)			11.93	nC
Gate-Source Charge	Q _{gs}		-	1.95	-	
Gate-Drain (Miller) Charge	Q _{gd}			6.85		

Note:

1. Pulse test: Pulse width ≤ 300μS, duty ≤ 2%

2. $S = \frac{1}{R}$

Electrical Characteristics (Control Part) (Continued)

(Ta = 25°C unless otherwise specified)

Characteristic	Symbol	Test condition	Min.	Typ.	Max.	Unit
UVLO SECTION						
Start Threshold Voltage	VSTART	VFB=GND	14	15	16	V
Stop Threshold Voltage	VSTOP	VFB=GND	8.4	9	9.6	V
OSCILLATOR SECTION						
Initial Accuracy	FOSC	KA5M0365RN	61	67	73	kHz
Initial Accuracy	FOSC	KA5L0365RN	45	50	55	kHz
Frequency Change With Temperature ⁽²⁾	-	-25°C≤Ta≤+85°C	-	±5	±10	%
Maximum Duty Cycle	Dmax		72	77	82	%
FEEDBACK SECTION						
Feedback Source Current	IFB	Ta=25°C, 0V≤Vfb≤3V	0.7	0.9	1.1	mA
Shutdown Feedback Voltage	VSD	Vfb≥6.5V	6.9	7.5	8.1	V
Shutdown Delay Current	Idelay	Ta=25°C, 5V≤Vfb≤VSD	4	5	6	μA
REFERENCE SECTION						
Output Voltage ⁽¹⁾	Vref	Ta=25°C	4.80	5.00	5.20	V
Temperature Stability ⁽¹⁾⁽²⁾	Vref/ΔT	-25°C≤Ta≤+85°C	-	0.3	0.6	mV/°C
CURRENT LIMIT(SELF-PROTECTION)SECTION						
Peak Current Limit	I _{OVER}	Max. inductor current	1.89	2.15	2.41	A
PROTECTION SECTION						
Over Voltage Protection	VOVP	VCC≥24V	25	27	29	V
Thermal Shutdown Temperature (Tj) ⁽¹⁾	TSD	-	140	160	-	°C
TOTAL STANDBY CURRENT SECTION						
Start-up Current	I _{START}	VCC=14V	-	100	170	μA
Operating Supply Current (Control Part Only)	I _{OP}	VCC≤28	-	7	12	mA

Note:

1. These parameters, although guaranteed, are not 100% tested in production
2. These parameters, although guaranteed, are tested in EDS(water test) process

Typical Performance Characteristics(SenseFET part) (Continued)
(KA5M0365RN, KA5L0365RN)

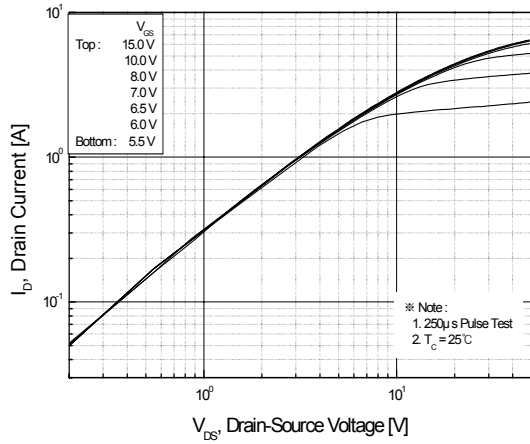


Figure 1. Output Characteristics

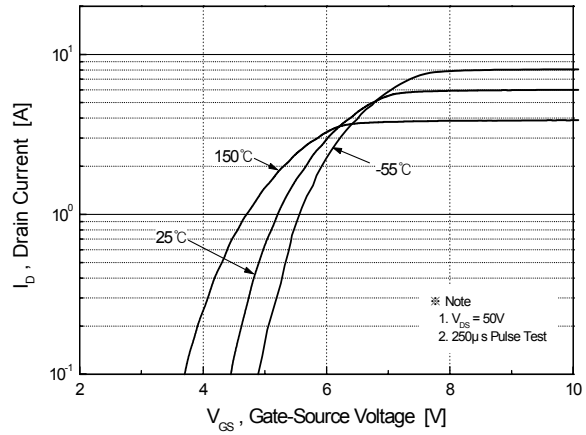


Figure 2. Transfer Characteristics

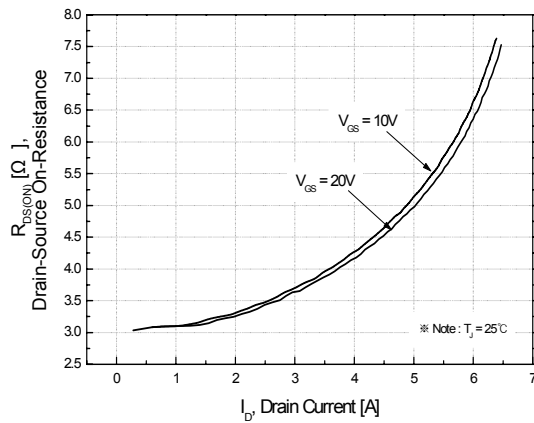


Figure 3. On-Resistance vs. Drain Current

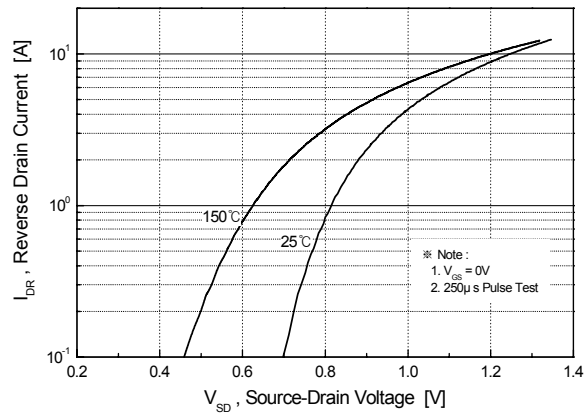


Figure 4. Source-Drain Diode Forward Voltage

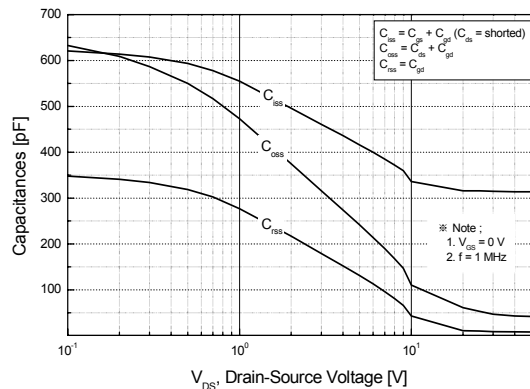


Figure 5. Capacitance vs. Drain-Source Voltage

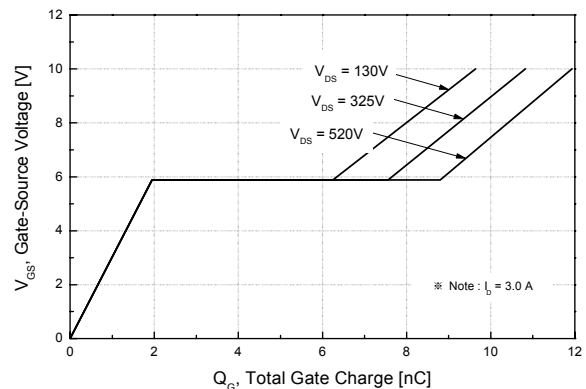


Figure 6. Gate Charge vs. Gate-Source Voltage

Typical Performance Characteristics (Continued)
 (KA5M0365RN, KA5L0365RN)

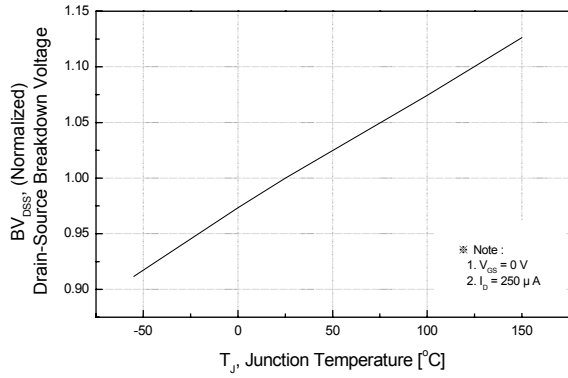


Figure 7. Breakdown Voltage vs. Temperature

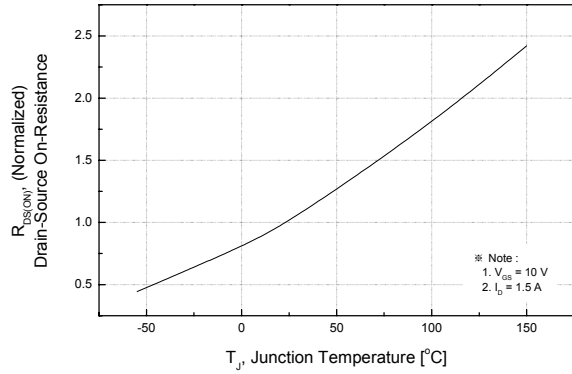


Figure 8. On-Resistance vs. Temperature

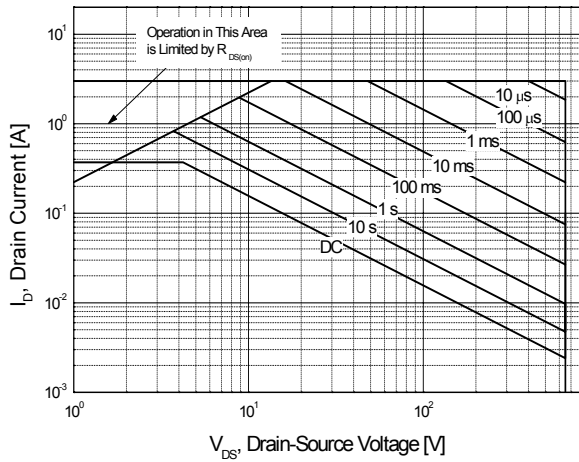


Figure 9. Max. Safe Operating Area

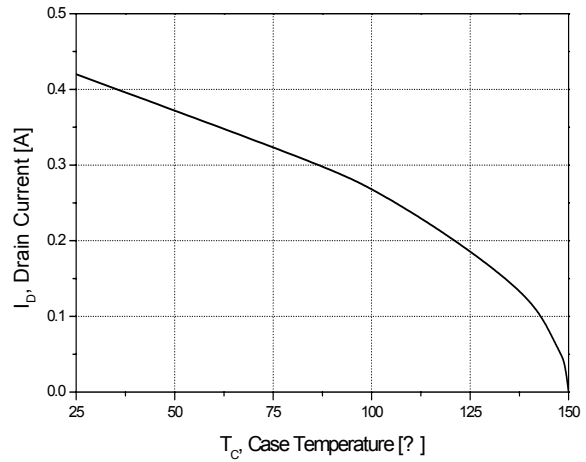


Figure 10. Max. Drain Current vs. Case Temperature

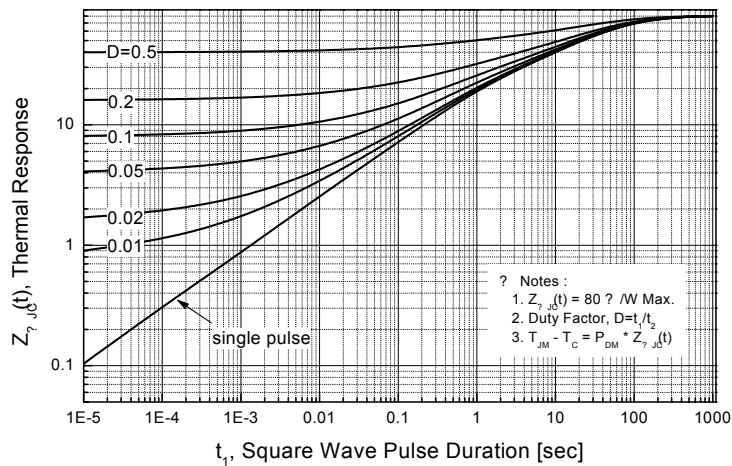


Figure 11. Thermal Response

Typical Performance Characteristics (Control Part) (Continued)

(These characteristic graphs are normalized at $T_a = 25^\circ\text{C}$)

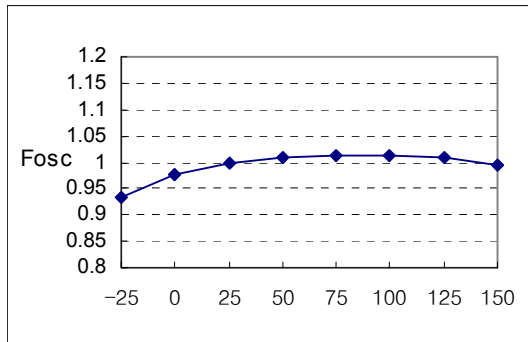


Figure 1. Operating Frequency

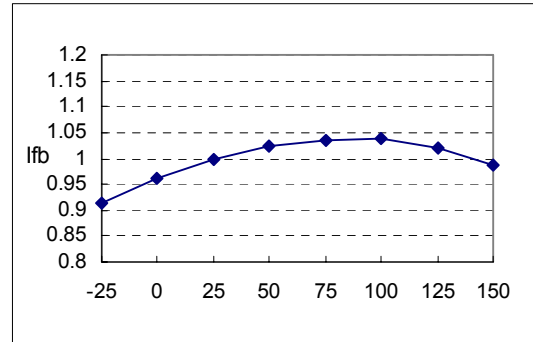


Figure 2. Feedback Source Current

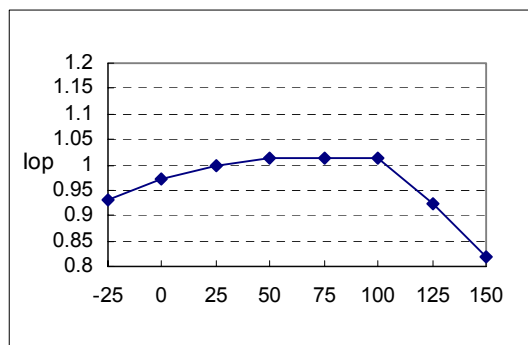


Figure 3. Operating Supply Current

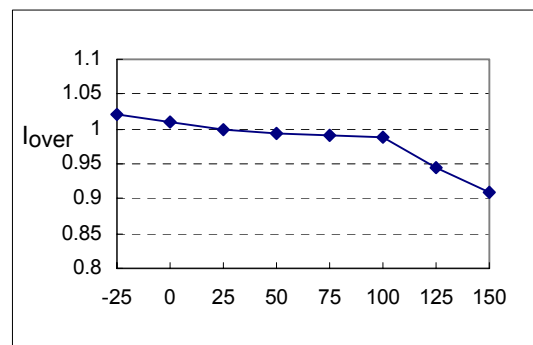


Figure 4. Peak Current Limit

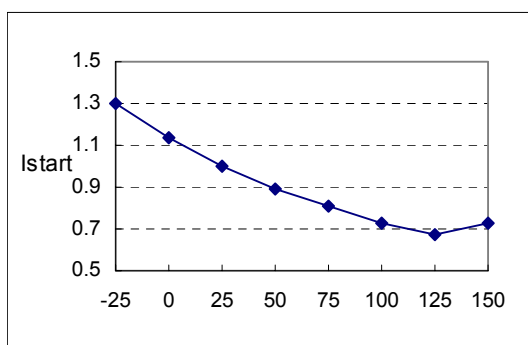


Figure 5. Start up Current

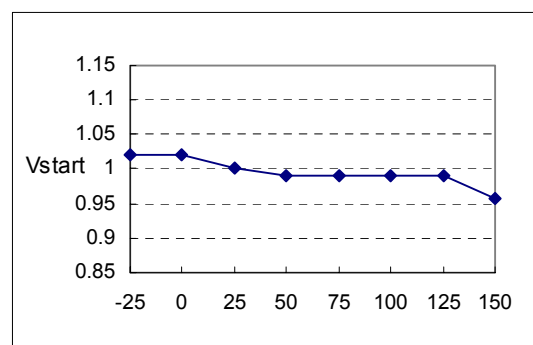


Figure 6. Start Threshold Voltage

Typical Performance Characteristics (Continued)

(These characteristic graphs are normalized at $T_a = 25^\circ\text{C}$)

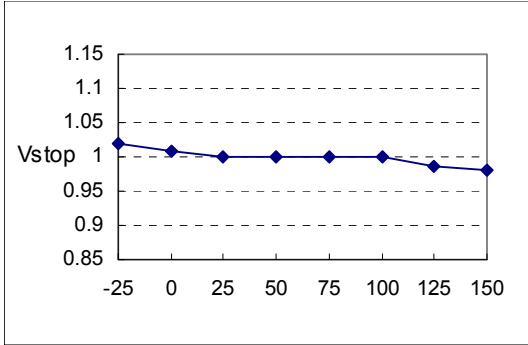


Figure 7. Stop Threshold Voltage

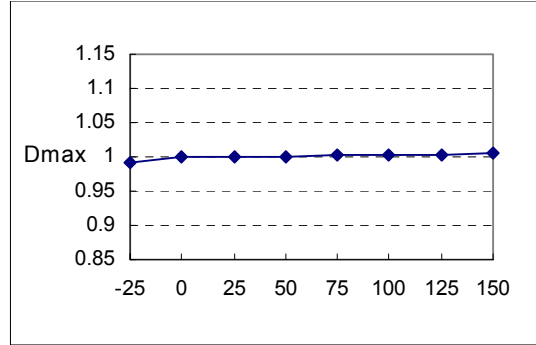


Figure 8. Maximum Duty Cycle

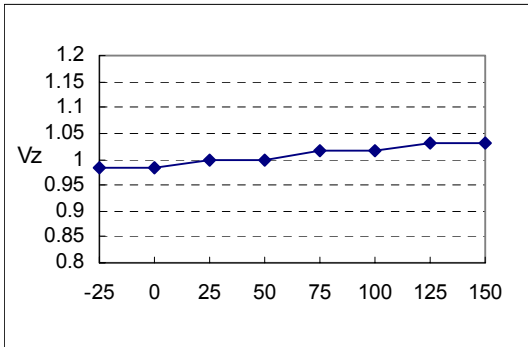


Figure 9. VCC Zener Voltage

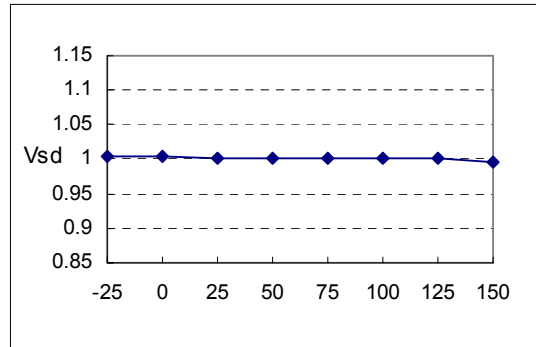


Figure 10. Shutdown Feedback Voltage

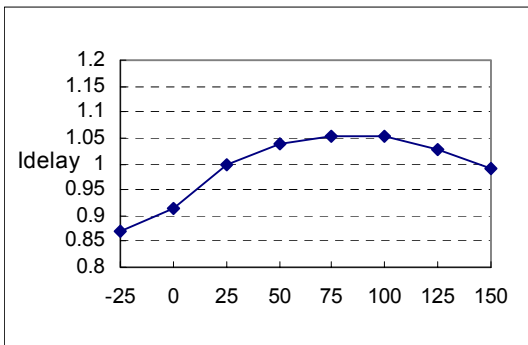


Figure 11. Shutdown Delay Current

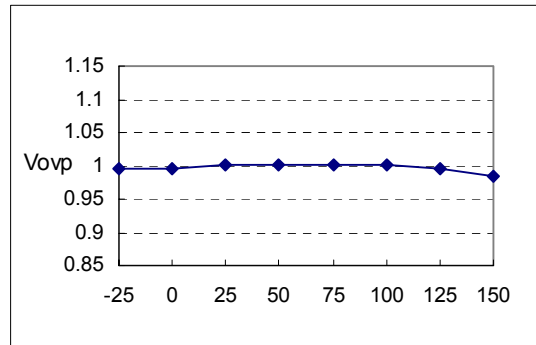


Figure 12. Over Voltage Protection

Typical Performance Characteristics (Continued)

(These characteristic graphs are normalized at $T_a = 25^\circ\text{C}$)

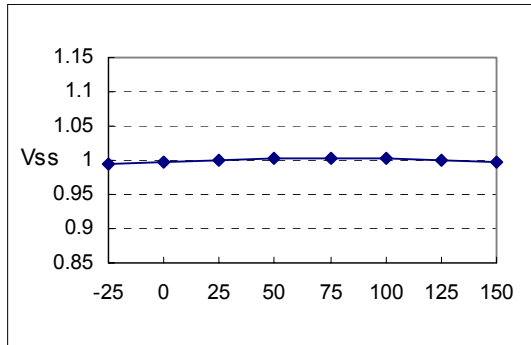


Figure 13. Soft Start Voltage

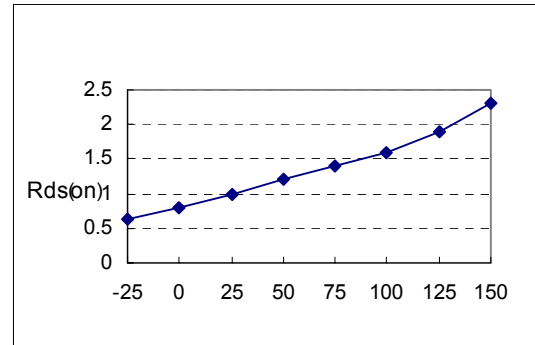
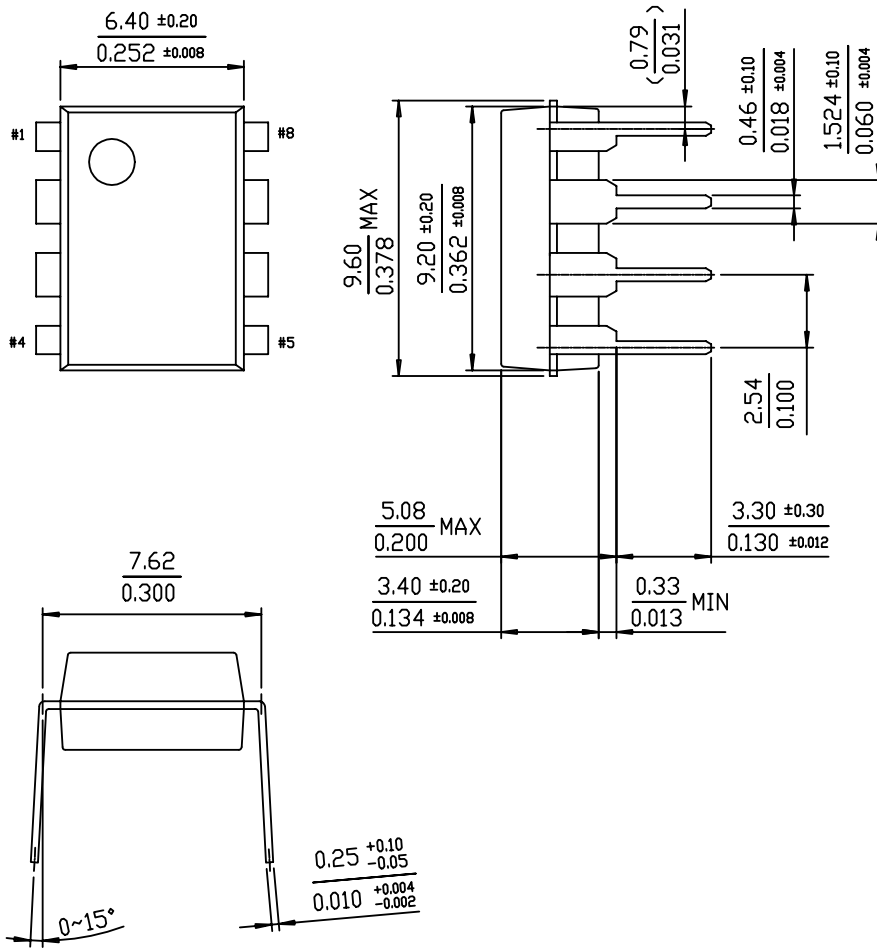


Figure 14. Static Drain-Source on Resistance

Package Dimensions

8-DIP



Ordering Information

Product Number	Package	Marking Code	BVDSS	FOSC	RDS(on)
KA5M0365RN	8-DIP	5M0365R	650V	67kHz	3.6Ω
KA5L0365RN	8-DIP	5L0365R	650V	50kHz	3.6Ω

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